

深圳市晶泰源电子有限公司

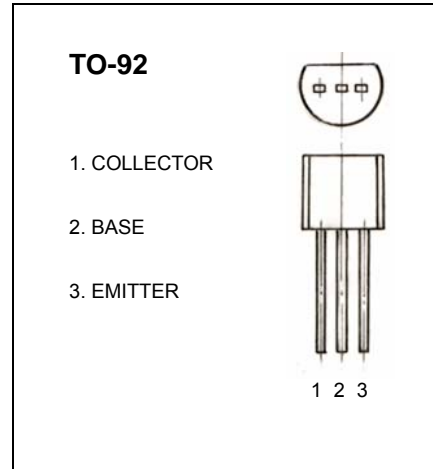
BC556/BC557/BC558 TRANSISTOR (PNP)

FEATURES

- High Voltage
- Complement to BC546/BC547/BC548

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	BC556 -80 BC557 -50 BC558 -30	V
	Collector-Emitter Voltage	-65 -45 -30	V
		Emitter-Base Voltage	-5
Collector Current -Continuous		-100	mA
P_C	Collector Power Dissipation	625	mW
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	BC556 BC557 BC558 V_{CBO}	$I_C = -100\mu\text{A}, I_E = 0$	-80 -50 -30			V
Collector-emitter breakdown voltage	BC556 BC557 BC558 V_{CEO}	$I_C = -2\text{mA}, I_B = 0$	-65 -45 -30			V
Emitter-base breakdown voltage	V_{EBO}	$I_E = -100\mu\text{A}, I_C = 0$	-5			V
Collector cut-off current	BC556 BC557 BC558 I_{CBO}	$V_{CB} = -70\text{V}, I_E = 0$ $V_{CB} = -45\text{V}, I_E = 0$ $V_{CB} = -25\text{V}, I_E = 0$			-0.1	μA
Collector cut-off current	BC556 BC557 BC558 I_{CEO}	$V_{CE} = -60\text{V}, I_B = 0$ $V_{CE} = -40\text{V}, I_B = 0$ $V_{CE} = -25\text{V}, I_B = 0$			-0.1	μA
Emitter cut-off current	BC556 BC557 BC558 I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$			-0.1	μA
DC current gain	BC556 BC557 BC558 BC557A BC556B/BC557B/BC558B BC557C h_{FE}	$V_{CE} = -5\text{V}, I_C = -2\text{mA}$	120 120 120 120 180 420		800 800 800 220 460 800	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}, I_B = -5\text{mA}$			-0.65	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100\text{mA}, I_B = -5\text{mA}$			-1	V
Transition frequency	f_T	$V_{CE} = -5\text{V}, I_C = -10\text{mA}$ $f = 100\text{MHz}$	150			MHz